REMARKS

Claims 1-10 are pending in this application. Amendments to claims 1 and 10 are proposed herein. The Applicants respectfully submit that no new matter has been added. It is believed that this Amendment is fully responsive to the Office Action dated June 30, 2003.

Claims 1-8 are rejected under 35 U.S.C. 103(a) as being anticipated [sic] by Ishikawa (U.S. Patent No. 6,294,446) in view of Udagawa et al. (U.S. Patent No. 6,462,361).

Applicants respectfully note that the Examiner apparently did not mean to use the term "anticipated" in the text of the rejection, since this is a rejection under 35 U.S.C. 103(a).

Reconsideration of the rejection is respectfully requested in view of the proposed amendment to claim 1. In the proposed amendment, the recitation of the "active element" in the active layer is clarified to a --high power active element for radio communication--. Support for this amendment may be found, for example, on page 11, lines 29-31, or page 12, lines 13-15, which indicate that the MESFETs function under high power conditions.

Applicants note that "lower and upper wide-band gap layers 33 and 35" in Ishikawa are different from the "active element" in present claim 1. The "active element" means an element such as a gate, source or drain.

Neither Ishikawa nor Udagawa et al. is related to "a high power semiconductor device" as recited in claim 1, and in particular, neither reference discloses "a high power active element for radio communication" in the active layer.

Fig. 2 of Ishikawa shows no turbulence in the curved lines in the high gate voltage domain (upper area in the graph). This indicates that the device of Ishikawa is not a high power device.

Udagawa et al. describes in column 24, lines 15-21: "The DC characteristics of the GaInP TEGFET **300** were evaluated. The saturated source-drain current (Ids) when a source/drain voltage of 3 Volts (V) was applied was found to be 70 milliampere (mA). When the drain voltage was swept from 0 V to 5 V, virtually no looping (hysteresis) in the drain current was observed." This indicates the device of Udagawa is not a high power device.

That is, the Ishikawa and Udagawa devices seem to be low-noise high-frequency FETs, much different from "high power device" claimed in present claim 1. These devices do not have "a high power active element for radio communication" as recited in the amended claims.

Applicants submit that claims 1-8, as amended, are novel and non-obvious over Ishikawa '446 and Udagawa et al. '361. Reconsideration of the rejection is again respectfully requested.

Claim 9 is rejected under 35 U.S.C. 103(a) as being anticipated [sic] by Ishikawa (U.S. Patent No. 6,294,446) in view of Udagawa et al. (U.S. Patent No. 6,462,361) and further in view of Usagawa et al. (U.S. Patent No. 5,373,191).

Applicants respectfully note that the Examiner apparently did not mean to use the term "anticipated" in the text of the rejection, since this is a rejection under 35 U.S.C. 103(a). Applicants also respectfully note that at the bottom of page 4, the Examiner apparently mistakenly refers to the Nitta reference, which was cited in the last Office action but is not cited in this rejection.

Reconsideration of the rejection is respectfully requested in view of the proposed amendment to claim 1. As noted above, the proposed amendment to claim 1 recites that the active layer has "a high power active element for radio communication formed therein." Neither Udagawa et al. '361 nor Ishikawa et al. '446 discloses a high power active element for radio communication.

Applicants similarly submit that Usagawa et al. '191 does not disclose a high power active element for radio communication. Therefore, no combination of the references can provide this limitation of claim 9.

Applicants therefore submit that with the proposed amendment to claim 1, claim 9 is novel and non-obvious over Ishikawa '446, Udagawa et al. '361 and Usagawa et al. '191, taken separately or in combination.

Claim 10 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form.

Claim 10 has been amended to be in independent form, incorporating the limitations of claim 1, from which it depended. Applicants submit that there is no change in the scope of claim 10 by this amendment.

In view of the aforementioned amendments and accompanying remarks, claims 1-10, as amended, are in condition for allowance, for which action, at an early date, is requested.

If for any reason, it is felt that this application is not now in condition for allowance, the Examiner is requested to contact Applicants' undersigned agent, at the telephone number indicated below, to arrange for an interview to expedite the disposition of this case.

In the event this response is not timely filed, Applicants respectfully petition for an appropriate extension of time. Please charge any fees for such an extension of time and any other fees which may be due with respect to this paper, to Deposit Account No. 01-2340.

Respectfully submitted,

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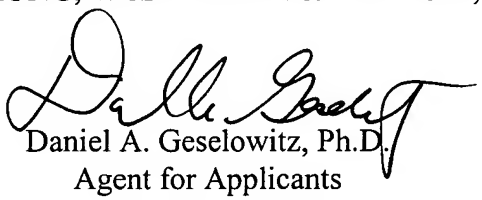

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